

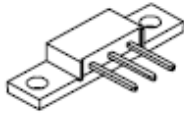
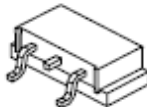
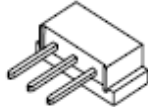
66CNQ200 SCHOTTKY RECTIFIER

Applications:

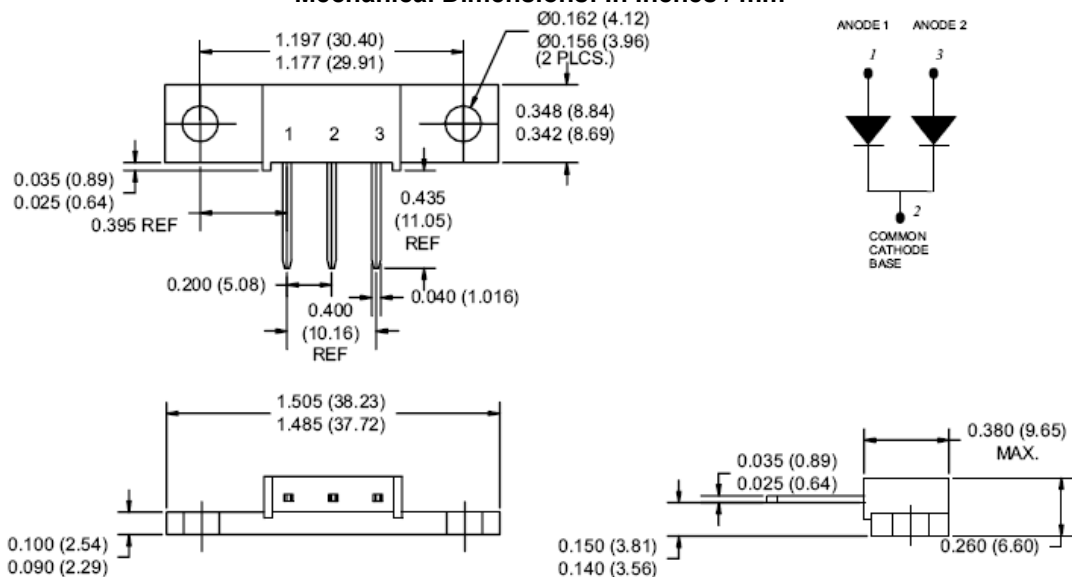
- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection

Features:

- 175°C T_J operation
- Center tap module
- Very Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- Low profile, high current package
- This is a Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

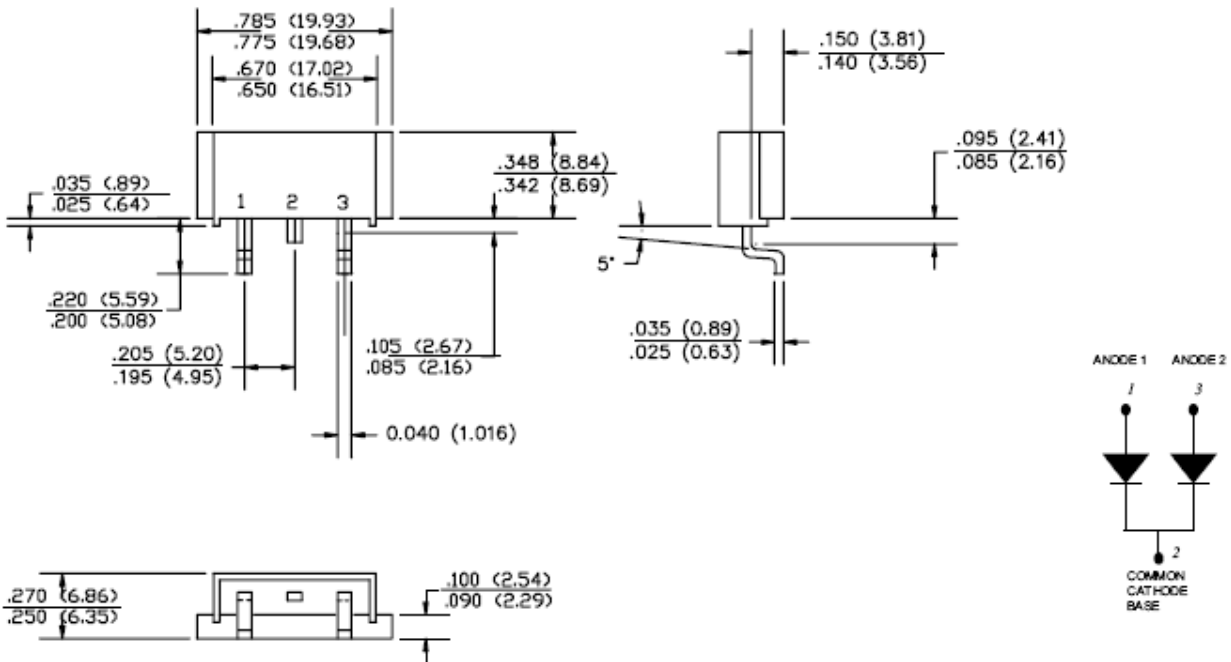
Case Styles		
66CNQ200	66CNQ200SL	66CNQ200SM
		
PRM3	PRM3-SL	PRM3-SM

Mechanical Dimensions: In Inches / mm

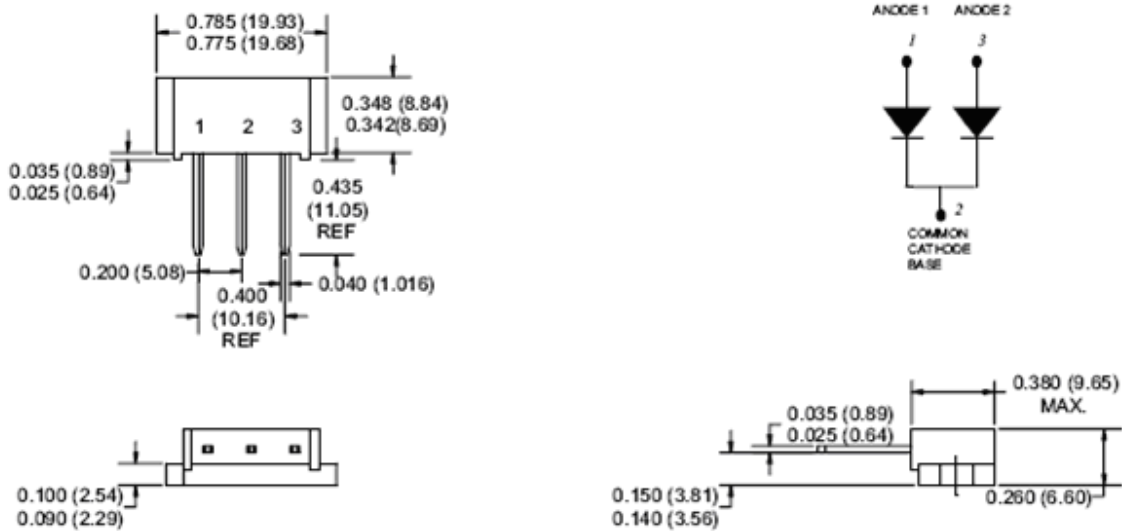


PRM3

- China - Germany - Korea - Singapore - United States •
- <http://www.smc-diodes.com> - sales@smc-diodes.com •



PRM3-SL



PRM3-SM

MARKING, MOLDING RESIN

Marking for 66CNQ200/SL/SM, 1st row SS YYWWL, 2nd row 66CNQ200/SL/SM, 3rd row 1 2 3 (pin)

Where YY is the manufacture year

WW is the manufacture week code

L is the wafer's Lot Number

Molding resin

Epoxy resin UL: 94V-0

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66CNQ200

Technical Data
Data Sheet N1056, Rev. -

Green Products

Ordering Information:

Device	Package	Terminals finish	Shipping
66CNQ200	PRM3	Nickel plated	48pcs / box
66CNQ200S	PRM3	Pure Sn dipped (dipped height 6-8 mm)	48pcs / box

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	-	200	V
Average Rectified Forward Current	$I_{F(AV)}$	50% duty cycle @ $T_C = 155^\circ\text{C}$, rectangular wave form	60	A
Peak One Cycle Non-Repetitive Surge Current (per leg)	I_{FSM}	8.3 ms, half Sine pulse	708	A

Electrical Characteristics:

Characteristics	Symbol	Condition	Typ.	Max.	Units
Forward Voltage Drop (per leg) *	V_{F1}	@ 30A, Pulse, $T_J = 25^\circ\text{C}$	0.80	0.92	V
	V_{F2}	@ 30A, Pulse, $T_J = 125^\circ\text{C}$	0.63	0.72	V
Reverse Current (per leg) *	I_{R1}	@ $V_R = \text{rated } V_R$ $T_J = 25^\circ\text{C}$	0.0002	1.5	mA
	I_{R2}	@ $V_R = \text{rated } V_R$ $T_J = 125^\circ\text{C}$	0.28	21	mA
Junction Capacitance (per leg)	C_T	@ $V_R = 5\text{V}$, $T_C = 25^\circ\text{C}$ $f_{SIG} = 1\text{MHz}$	750	900	pF
Series Inductance (per leg)	L_S	Measured lead to lead 5 mm from package body	6.0	-	nH
Voltage Rate of Change	dv/dt	-	-	10,000	V/ μs

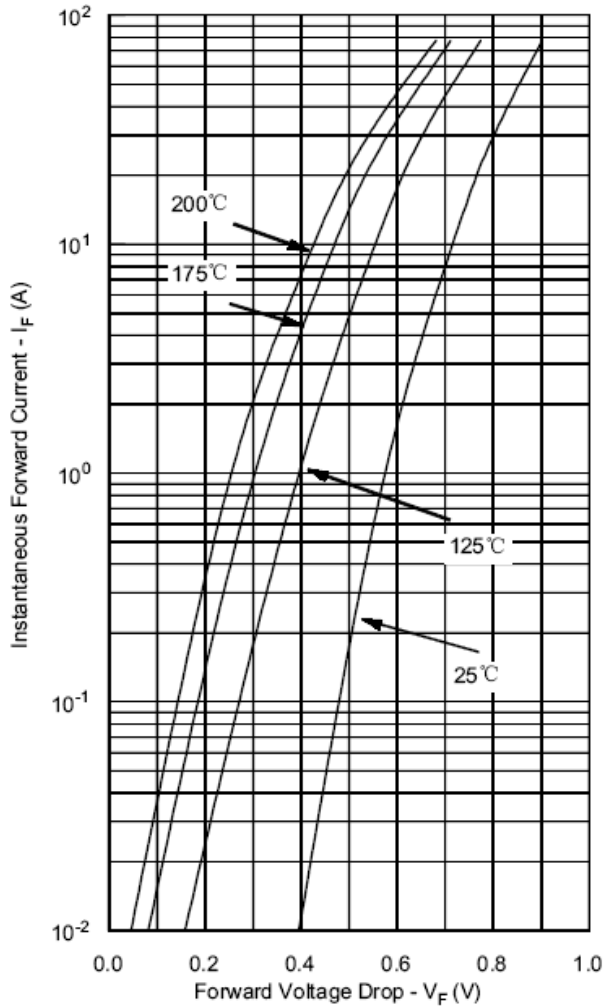
* Pulse Width < 300 μs , Duty Cycle <2%

Thermal-Mechanical Specifications:

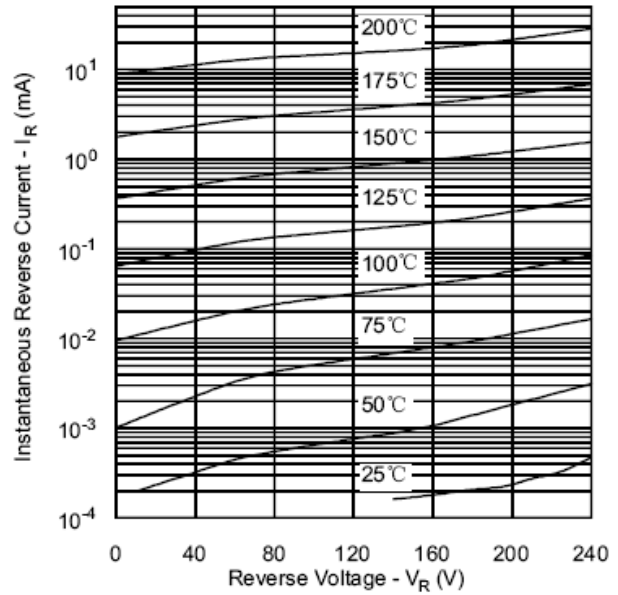
Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	T_J	-	-55 to +175	$^\circ\text{C}$
Storage Temperature	T_{stg}	-	-55 to +175	$^\circ\text{C}$
Typical Thermal Resistance Junction to Case(per leg)	$R_{\theta JC}$	DC operation	0.85	$^\circ\text{C/W}$
Typical Thermal Resistance Junction to Case (per package)	$R_{\theta JC}$	DC operation	0.42	$^\circ\text{C/W}$
Typical Thermal Resistance, case to Heat Sink	$R_{\theta cs}$	Mounting surface, smooth and greased	0.30	$^\circ\text{C/W}$
Mounting Torque	T_M	-	40(min)	Kg-cm
			58(max)	
Approximate Weight	wt	-	7.8	g
Case Style	PRM3 PRM3-SL PRM3-SM			

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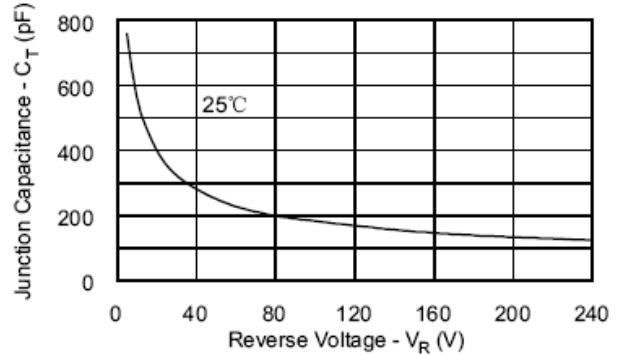
Typical Forward Characteristics



Typical Reverse Characteristics



Typical Junction Capacitance





66CNQ200

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